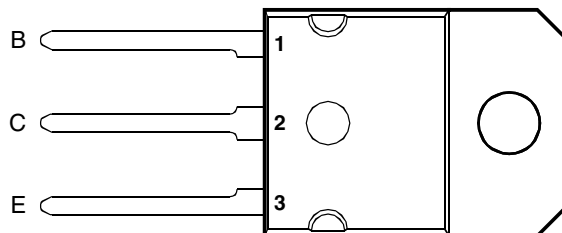


- Designed for Complementary Use with TIP145, TIP146 and TIP147
- 125 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 5 A

SOT-93 PACKAGE
(TOP VIEW)



MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	TIP140	V_{CBO}	60	V
	TIP141		80	
	TIP142		100	
Collector-emitter voltage ($I_B = 0$)	TIP140	V_{CEO}	60	V
	TIP141		80	
	TIP142		100	
Emitter-base voltage		V_{EBO}	5	V
Continuous collector current		I_C	10	A
Peak collector current (see Note 1)		I_{CM}	15	A
Continuous base current		I_B	0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	125	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	100	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	260	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 1 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20$ mH, $I_{B(on)} = 5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$ (see Note 5)	$I_B = 0$	TIP140 TIP141 TIP142	60 80 100			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$ $V_{CE} = 40 \text{ V}$ $V_{CE} = 50 \text{ V}$	$I_B = 0$ $I_B = 0$ $I_B = 0$	TIP140 TIP141 TIP142			2 2 2	mA
I_{CBO} Collector cut-off current	$V_{CB} = 60 \text{ V}$ $V_{CB} = 80 \text{ V}$ $V_{CB} = 100 \text{ V}$	$I_E = 0$ $I_E = 0$ $I_E = 0$	TIP140 TIP141 TIP142			1 1 1	mA
I_{EBO} Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = 4 \text{ V}$ $V_{CE} = 4 \text{ V}$	$I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)	1000 500			
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = 10 \text{ mA}$ $I_B = 40 \text{ mA}$	$I_C = 5 \text{ A}$ $I_C = 10 \text{ A}$	(see Notes 5 and 6)			2 3	V
V_{BE} Base-emitter voltage	$V_{CE} = 4 \text{ V}$	$I_C = 10 \text{ A}$	(see Notes 5 and 6)			3	V
V_{EC} Parallel diode forward voltage	$I_E = 10 \text{ A}$	$I_B = 0$	(see Notes 5 and 6)			3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = 10 \text{ A}$	$I_{B(on)} = 40 \text{ mA}$	$I_{B(off)} = -40 \text{ mA}$		0.9		μs
t_{off} Turn-off time	$V_{BE(off)} = -4.2 \text{ V}$	$R_L = 3 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$		11		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

**TYPICAL DC CURRENT GAIN
vs
COLLECTOR CURRENT**

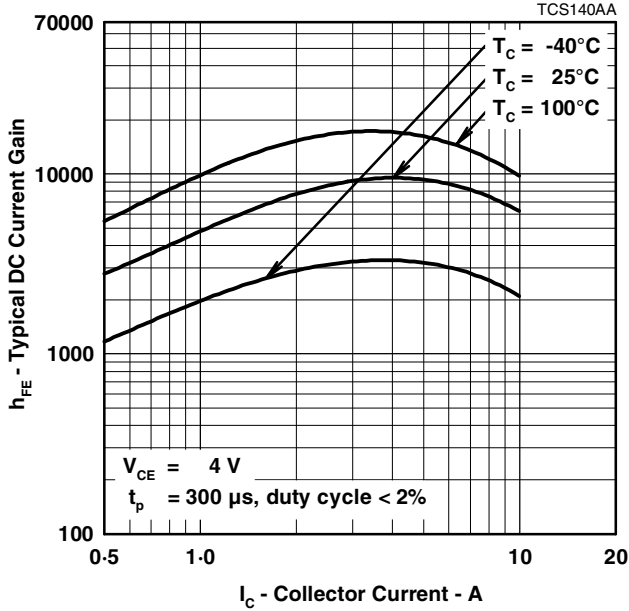


Figure 1.

**COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT**

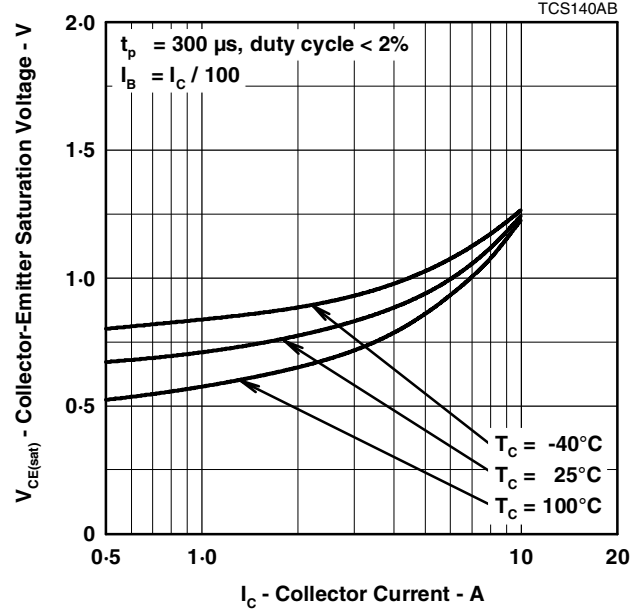


Figure 2.

**BASE-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT**

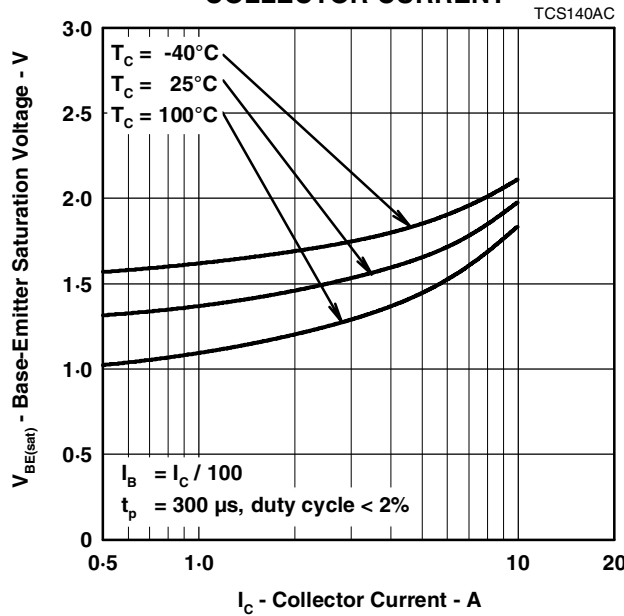


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

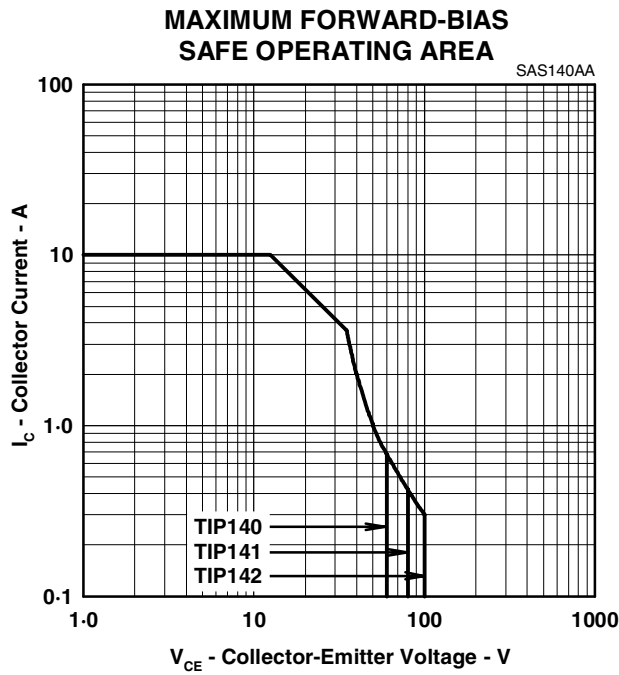


Figure 4.

THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**

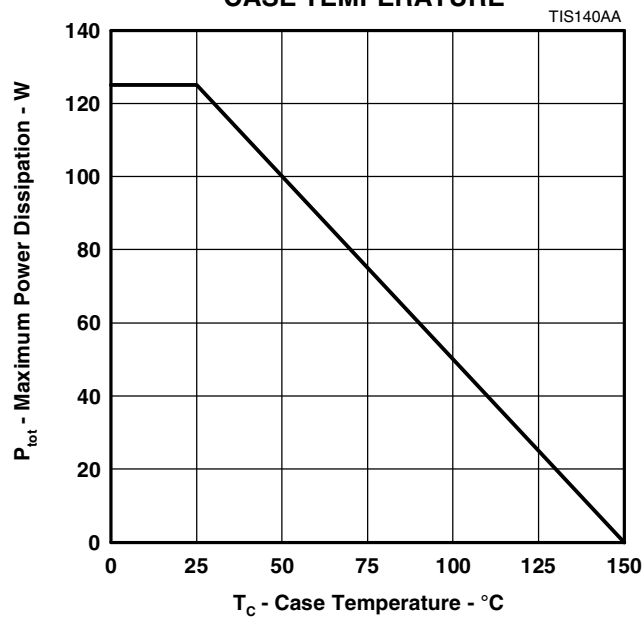


Figure 5.

PRODUCT INFORMATION